



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	40mΩ @ V _{GS} = 4.5V	5.0A
30V	75mΩ @ V _{GS} = 2.5V	3.6A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

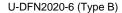
Description and Applications

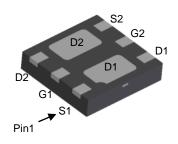
This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

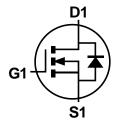
- **Battery Charging**
- **Power Management Functions**
- DC-DC Converters
- Portable Power Adaptors

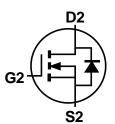
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)









Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3055LFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMN3055LFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1



M6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D	 Н	I	J	K	L	М	N	0	Р	R

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



M6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	 0	1	2	3	4	5	6	7	8	9

Ī	Week	1-26	27-52	53
ĺ	Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Χ	Υ	Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			lo	5.0 4.0	Α
Maximum Continuous Body Diode Forward Currer	nt (Note 6)		Is	1.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	IDM	25	Α	
Avalanche Current (Note 7) L = 0.1mH		las	11	Α	
Avalanche Energy (Note 7) L = 0.1mH			Eas	6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	Pn	0.81	W	
Total Fower Dissipation (Note 5)	T _A = +70°C	PD	0.52		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	132	°C/W	
Thermal Resistance, sunction to Ambient (Note 3)	t<10s	RθJA	101		
Total Power Dissipation (Note 6)	T _A = +25°C	Pp	1.36	W	
Total Fower Dissipation (Note o)	T _A = +70°C	רט	0.87		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Davi	83		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	Reja	60	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	10			
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

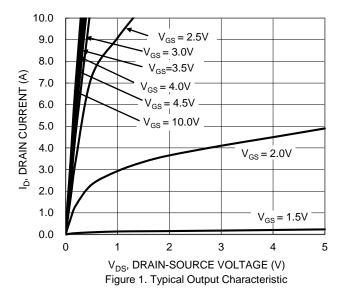
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)				1		1	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current, TJ = +25°C	IDSS	_	_	1.0	μΑ	V _{DS} = 30V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Descou	l	32	40	mΩ	$V_{GS} = 4.5V, I_{D} = 3A$	
Static Drain-Source On-Resistance	RDS(ON)	_	52	75	11177	V _{GS} = 2.5V, I _D = 2A	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	l	458		рF	151/11/ 01/	
Output Capacitance	Coss	l	50		рF	V _{DS} = 15V, V _{GS} = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	1	44	_	рF	1 = 1.0101112	
Gate Resistance	Rg	_	2.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	1	11.2	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	5.3	_	nC	\/ 45\/ I- 4A	
Gate-Source Charge	Qgs	_	1.1	_	nC	$V_{DS} = 15V, I_{D} = 4A$	
Gate-Drain Charge	Qgd	_	1.8	_	nC		
Turn-On Delay Time	tD(ON)	_	1.8	_	ns		
Turn-On Rise Time	t _R	_	2.6	_	ns	V _{DS} = 15V, V _{GS} = 10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	9.5	_	ns	$R_g = 6\Omega$, $R_L = 3.75\Omega$	
Turn-Off Fall Time	tF	_	2.1	_	ns		
Reverse Recovery Time	trr		7.0	_	ns	I_ 24 di/dt 1004/up	
Reverse Recovery Charge	Q _{RR}	ı	1.8	_	nC	$I_F = 3A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Device mounted on FR-4 substrate PC board, 202 copper, with minimum ecommended particles.
Device mounted on FR-4 substrate PC board, 202 copper, with 1inch square copper plate.
I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.





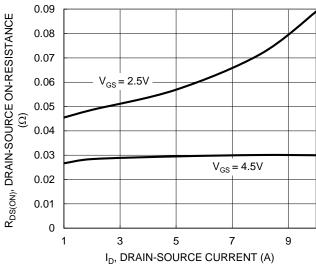


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

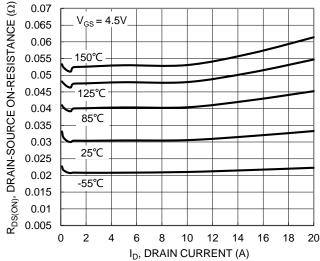


Figure 5 . Typical On-Resistance vs. Drain Current and Temperature

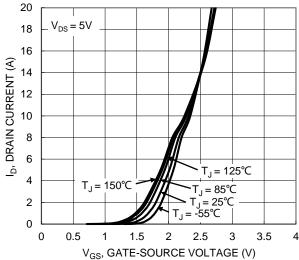


Figure 2. Typical Transfer Characteristic

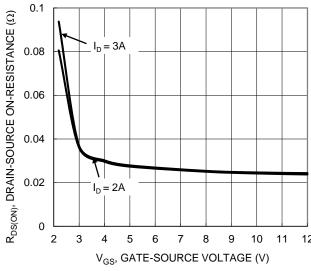


Figure 4 . Typical Transfer Characteristic

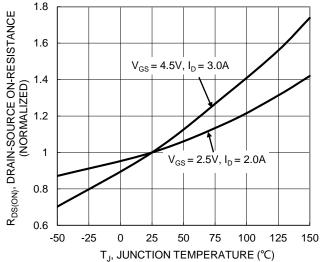


Figure 6. On-Resistance Variation with Temperature



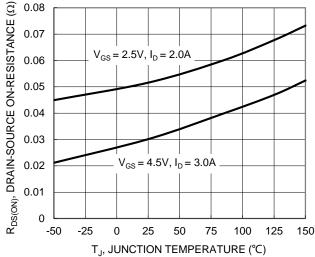


Figure 7. On-Resistance Variation with Temperature

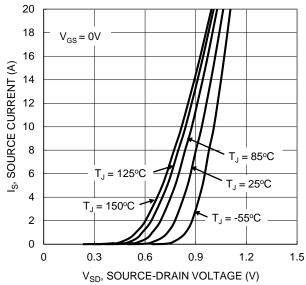


Figure 9. Diode Forward Voltage vs. Current

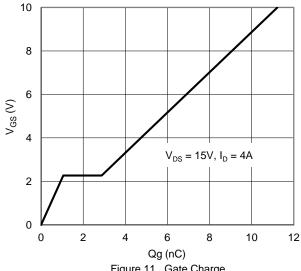


Figure 11. Gate Charge

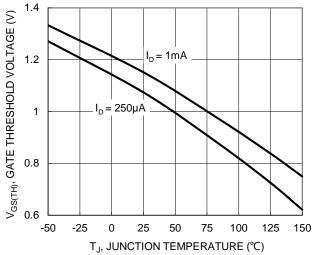
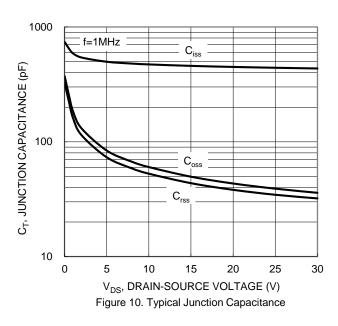


Figure 8. Gate Threshold Variation vs. Junction Temperature



100 $R_{DS(ON)}$ Limited $P_w = 100 \mu s$ ID, DRAIN CURRENT (A) 10 0.1 $T_{J(Max)} = 150$ °C Single Pulse DUT on 1*MRP Board 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



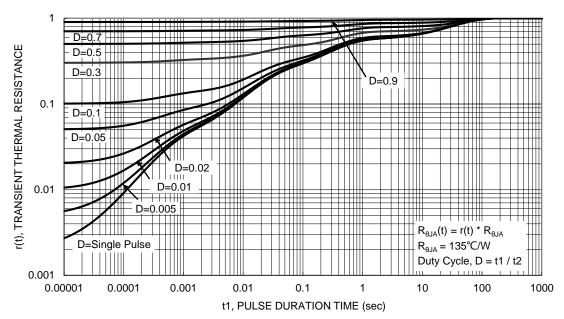


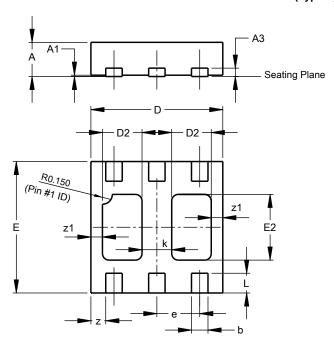
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

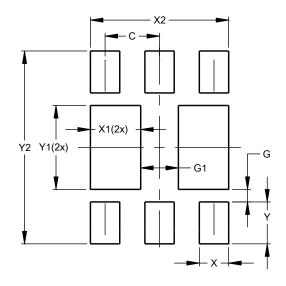


	U-DFN (Typ		
Dim	Min	Max	Тур
Α	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
е	-	-	0.65
Е	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
Z	-	-	0.225
z1	-	-	0.175
All	Dimens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value
Dillicitorio	(in mm)
С	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com

DMN3055LFDB Document number: DS38172 Rev. 3 - 2 Downloaded From Oneyac.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))